

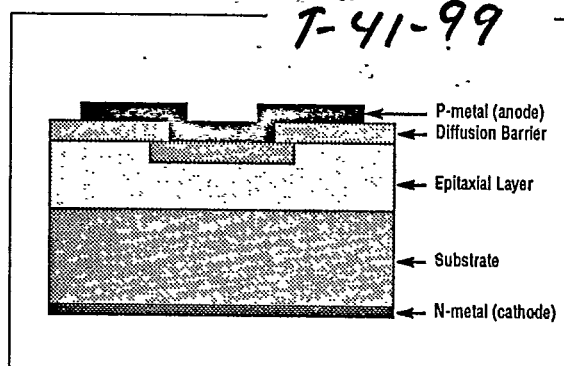
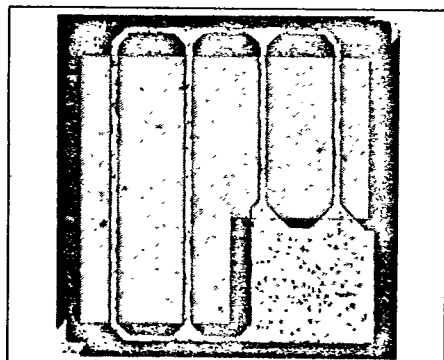
SIEMENS

RP-13B

Mask-Diffused GaAsP

Point Source LED

PART NO. 2600-7074

**DESCRIPTION**

Siemens RP-13B is a mask-diffused GaAsP point source light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for lamps or dot-matrix displays.

MATERIAL

Epitaxial Layer: GaAs_{1-x}P_x : Te
 Substrate: GaAs : Si or GaAs : Te
 Metalizations: Anode Aluminum
 Cathode Gold-Germanium

Dimensions

(center to center): Height 0.015"
 Width 0.015"
 Thickness 0.010"

TYPICAL DEVICE PARAMETERS

Forward I-V Characteristics	V_{F3}	1.64 V	@ 20 mA
	V_{F2}	1.59 V	@ 10 mA
	V_{F1}	1.42 V	@ 100 μ A
Reverse I-V Characteristics	V_{R1}	-25.0 V	@ -10 μ A
Peak EL Wavelength	λ	655 nm	@ 20 mA
Spectral Half-Width	FWHM	40 nm	@ 20 mA
Luminous Intensity (Device does not have AR coating)	LI	450 μ Cd	@ 10 mA